

# TRANSPARENT OXIDE ELECTRONICS

From Materials to Devices

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 WILEY

This edition first published 2012  
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John Wiley & Sons, Ltd, The Atrium, Southern Gate, Chichester, West Sussex, PO19 8SQ, United Kingdom

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*Library of Congress Cataloging-in-Publication Data*

Transparent oxide electronics : from materials to devices / Pedro Barquinha ... [et al.].

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